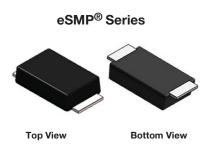
# VS-3EYH01-M3, VS-3EYH02-M3

**Vishay Semiconductors** 





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SlimSMAW (DO-221AD)

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**DESIGN SUPPORT TOOLS** 



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	3 A					
V <sub>R</sub>	100 V, 200 V					
V <sub>F</sub> at I <sub>F</sub>	0.71 V					
I <sub>FSM</sub>	70 A					
t <sub>rr</sub> (typ.)	16 ns					
T <sub>J</sub> max.	175 °C					
Package	SlimSMAW (DO-221AD)					
Circuit configuration	Single					

#### FEATURES

- Low profile package
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compatible to SOD-128 package case outline
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial, and automotive applications.

### **MECHANICAL DATA**

#### Case: SlimSMAW

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Polarity: color band denotes the cathode end

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
VS-3EYH01-M3		<b>M</b>		100	V		
Peak repetitive reverse voltage	VS-3EYH02-M3	V <sub>RRM</sub>		200	v		
Average rectified forward current		I <sub>F(AV)</sub> <sup>(1)</sup>	T <sub>C</sub> = 137 °C	3	A		
Non-repetitive peak surge current		I <sub>FSM</sub>	$T_J$ = 25 °C, 10 ms sine pulse wave	70			
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C		

Note

<sup>(1)</sup> Mounted on infinite heatsink

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking	VS-3EYH01-M3	$V_{BR}$ , $V_{R}$	- I <sub>B</sub> = 100 μA	100	-	-	v	
voltage	VS-3EYH02-M3		$R = 100 \mu A$	200	-	-		
Forward voltage, per diode		V <sub>F</sub>	I <sub>F</sub> = 3 A	-	0.86	0.95		
			I <sub>F</sub> = 3 A, T <sub>J</sub> = 150 °C	-	0.71	0.79		
Reverse leakage current, per diode		I <sub>R</sub>	$V_R = V_R$ rated	-	-	2		
			$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	20	μA	
Junction capacitance		CT	V <sub>R</sub> = 200 V	-	16	-	pF	

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COMPLIANT

HALOGEN

FREE

# VS-3EYH01-M3, VS-3EYH02-M3



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### **Vishay Semiconductors**

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	= 50 A/μs, V <sub>R</sub> = 30 V	-	22	-		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	100 A/ $\mu$ s, V <sub>R</sub> = 30 V	-	16	-		
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1A,	I <sub>rr</sub> = 0.25 A	-	-	30	ns	
		T <sub>J</sub> = 25 °C		-	18	-		
		T <sub>J</sub> = 125 °C		-	30	-		
Deck recover a current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 3 A$ ,	-	2.5	-	A nC	
Peak recovery current		T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 200 A/µs, V <sub>R</sub> = 100 V	-	4	-		
	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	23	-		
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	60	-		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C	
Thermal resistance, junction to mount		R <sub>thJM</sub> <sup>(1)</sup>	Infinite heatsink	-	12	15		
Thermal resistance, junction to ambient		R <sub>thJA</sub>	Device mounted on FR4 PCB, 2 oz. standard footprint	· - 120		150	°C/W	
VS-3EYH01-M3				3H1				
Marking device	VS-3EYH02-M3		Case style SlimSMAW (DO-221AD)		3H2			

#### Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC<sup>®</sup> 51-14 transient dual interface test method (TDIM)

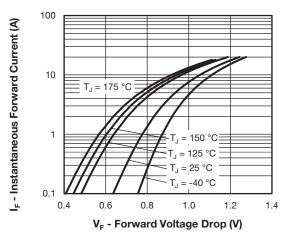


Fig. 1 - Typical Forward Voltage Drop Characteristics

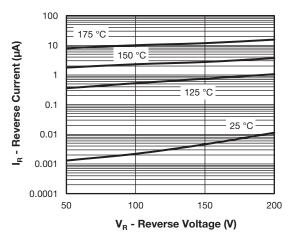
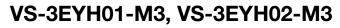


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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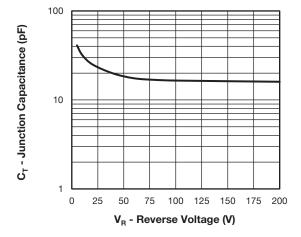


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

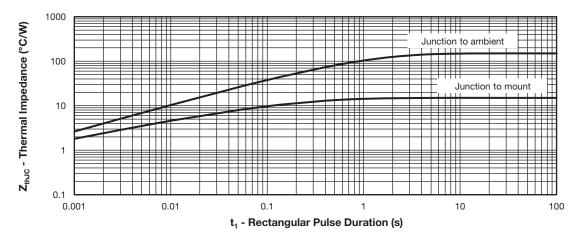
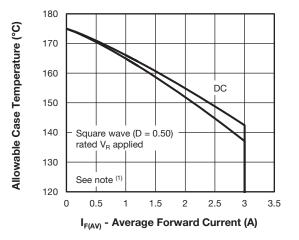
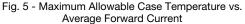


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics



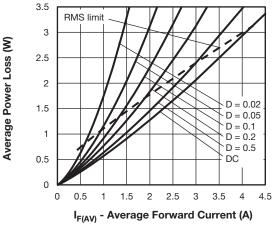
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#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 





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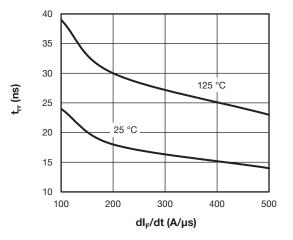
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# VS-3EYH01-M3, VS-3EYH02-M3

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Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

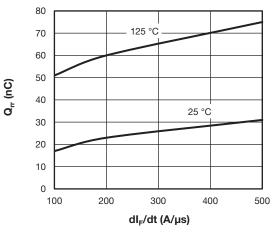


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

### **ORDERING INFORMATION TABLE**

Device code	VS-	3	Е	Y	н	02	-	М3	
		2	3	4	5	6		7	
	1 2 3	- Cur - Circ	rent rati	niconduo ng (3 = : iguratior liode	3 A)	oduct			
	4 - 5 -	- Pro	cess typ			)			
	6 - 7 -	- Volt	age coo	ist recov le (02 = en-free,	200 V)	complia	nt, and	termina	tions lead (Pt

ORDERING INFORMATION (Example)										
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	PACKAGING DESCRIPTION						
VS-3EYH01-M3/H	0.033	н	3500	7"diameter plastic tape and reel						
VS-3EYH01-M3/I	0.033	I	14 000	13"diameter plastic tape and reel						
VS-3EYH02-M3/H	0.033	Н	3500	7"diameter plastic tape and reel						
VS-3EYH02-M3/I	0.033	I	14 000	13"diameter plastic tape and reel						

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96582					
Part marking information	www.vishay.com/doc?95562					
Packaging information	www.vishay.com/doc?88869					
SPICE model	www.vishay.com/doc?96586					

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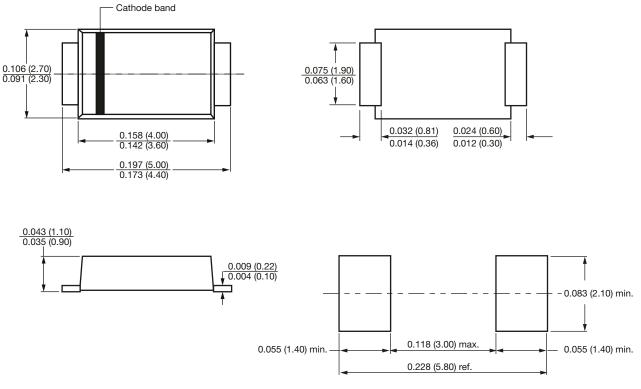
### **Outline Dimensions**

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# SlimSMAW (DO-221AD)

### **DIMENSIONS** in inches (millimeters)

SlimSMAW (DO-221AD)



Mounting pad layout





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